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Substitute for form 1449B/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

### Complete if Known

Application Number	10/822,343
Filing Date	April 12, 2004
First Named Inventor	Meng Tao
Group Art Unit	2812
Examiner Name	Not Yet Assigned
Attorney Docket Number	124263-1020

### OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TMS	1	R.M. TROMP, R.J. HAMERS, and J.E. DEMUTH, Si(001) dimmer structure observed with scanning tunneling microscopy, Phys. Rev. Lett., 1985, 1303, 55	
	2	E. KAXIRAS, Semiconductor-surface restoration by valence-mending absorbates: Application to Si(100):S and Si(100):Se, Physical Review B, 1991, 6324, 43	
	3	H. METZNER, TH. HALN, and J.-H. BREMER, Structure of sulfur-terminated silicon surfaces, Surf. Sci., 1997, 377-371-374, 379,	
	4	J.J. BOLAND, Structure of the H-saturated Si(100) surface, Phys. Rev. Lett., 1990, 3325, 65	
	5	M. TAO and L.P. HUNT, The thermodynamic behavior of the Si-H system and its role in Si-CVD from SiH <sub>4</sub> , J. Electrochem. Soc., 1992, 806, 139	
	6	J.E. NORTHRUP, Structure of Si(100)H: Dependence on the H chemical potential, Phys. Rev. B, 1991, 1419, 44	
	7	B.S. MEYERSON, F.J. HIMPSEL, and K. J. URAM, Bistable conditions for low-temperature silicon epitaxy, Appl. Phys. Lett., 1990, 1034, 57	
	8	J.W. LYDING, T.-C SHEN, J.S. HUBACEK, J.R. TUCKER, and G.C. ABELN, Nanoscale patterning and oxidation of H-passivated Si(100)-2x1 surfaces with an ultrahigh vacuum scanning tunneling microscope, Appl. Phys. Lett., 1994, 2010, 64	
	9	T.-C SHEN, C. WANG, G.C. ABELN, J.R. TUCKER, J.W. LYDING, PH. AVOURIS, and R.E. WALKUP, Atomic-scale desorption through electronic and vibrational excitation mechanisms, Science, 1995, 1590, 268	
V	10	J.W. LYDING, UHV STM nanofabrication: progress, technology spin-offs, and challenges, Proceedings of the IEEE, 1997, 589, 85	
TMS	11	T.-C. SHEN, C. WANG, and J.R. TUCKER, Al nucleation on monohydride and bare Si (001) surfaces: atomic scale patterning, Phys. Rev. Lett., 1997, 1271, 78	

Examiner Signature

*Michael H. Speer*

Date Considered

04/06

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

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Sheet	2	of	2	Attorney Docket Number	124283-1020

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MS	12	I. LYUBINETSKY, Z. DOHNALEK, W.J. CHOYKE, and J.T. YATES, JR., C1 <sub>2</sub> dissociation on Si(100)-(2x1): A statistical study by scanning tunneling microscopy, Phys. Rev. B, 1998, 7950, 58	
	13	M. CHANDER, Y.Z. LI, D. RIOUX, and J.H. WEAVER, Patterning of Si(100): Spontaneous etching with Br <sub>2</sub> , Phys. Rev. Lett., 1993, 4154, 71	
	14	The National Technology Roadmap for Semiconductors, Semiconductor Industry Association, 1997	
	15	A. M. COWLEY, S. M. SZE, Surface States and Barrier Height of Metal-Semiconductor Systems, J. Appl. Phys, 1965, 3212-3220, 36	
	16	J. P. LACHARME, N. BENAZZI, C. A. SEBENNE, Compositional and electronic properties of Si(001)2X1 upon diatomic sulfur interaction, Surf. Sci., 1999, 415-419, 433-435	
	17	A. C. PAPAGEORGOPOULOS, M. KAMARATOS, Adsorption and desorption of Se on Si(100)2X1: surface restoration, Surf. Sci., 1999, 415-419, 433-435	
MS	18	MICHAELSON, HERBERT B., The work function of the elements and its periodicity, J. Appl. Phys., 1977, 4729-33, 48	

Examiner Signature	<i>Y. M. S. Chen</i>	Date Considered	04/06
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